Docket No.

243579US0X/atp

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Tetsuo SUZUKI, et al.

SERIAL NO:

10/677,309

GAU:

FILED:

October 3, 2003

**EXAMINER:** 

FOR:

METHOD OF RECLAIMING SILICON WAFERS

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

#### REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

### RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

#### **CERTIFICATION**

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

### **DEPOSIT ACCOUNT**

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number <u>15-0030</u>. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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## STATEMENT OF RELEVANCY

## Reference AI (JP 2002-270568) on Form PTO 1449:

This reference relates to a method of manufacturing semiconductor wafer and metal monitoring device.

## Reference AJ (JP 2002-158207) on Form PTO 1449:

This reference relates to a method of recycling silicon single crystal wafer with copper films and recycled wafer.

## Reference AK (JP 2001-213694) on Form PTO 1449:

This reference relates to a semiconductor wafer with low copper content.

## Reference AL (JP 2001-174375) on Form PTO 1449:

This reference relates to a wafer for evaluation of metal contamination and method therefore.

## Reference AM (JP 2000-164558) on Form PTO 1449:

This reference relates to a method for reproducing silicon wafer with metal film.

## **Reference AN (JP 9-064133) on Form PTO 1449:**

This reference relates to a detecting method of Cu concentration in semiconductor substrate.

## Reference AO (JP 9-017833) on Form PTO 1449:

This reference relates to an evaluation method and regeneration method for semiconductor wafer, and its device.

## Reference AP (JP 7-122532) on Form PTO 1449:

This reference relates to a production of regenerated wafer.

## Reference AQ (JP 6-168998) on Form PTO 1449:

This reference relates to an evaluating method for contamination.

## Reference AR (JP 5-315428) on Form PTO 1449:

This reference relates to an estimation method of contamination impurities.



SHEET 1 OF 1

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Form PTO 1449 (Modified)	_	U.S. DEPARTMENT ( PATENT AND TRAD		ATTY DOCKET NO.		SERIAL N		<u></u>		
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				U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		ILING DATE APPROPRIATE		
	AA	6,451,696	09/17/2002	Y. HARA, et al.	<u></u>					
	AB	6,406,923	06/18/2002	H. INOUE, et al.	<u> </u>					
	AC	6,384,415	05/07/2002	T. SUZUKI, et al.						
	AD	5,885,334	03/23/1999	T. SUZUKI, et al.	<u> </u>	<u> </u>				
	AE	5,855,735	01/05/1999	S. TAKADA, et al.	'					
	AF	5,622,875	04/22/1997	J. E. LAWRENCE	† · · · · ·					
	AG	3,923,567	12/02/1975	J. E. LAWRENCE						
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			FO	REIGN PATENT DOCUMENTS	<u></u>					
		DOCUMENT NUMBER	DATE	COUNTRY		1	TRANSLATIO YES			
	AI	2002-270568	09/20/2002	JAPAN (with English Abstract)				NO X		
	AJ	2002-158207	05/31/2002	JAPAN (with English Abstract)				X		
	AK	2001-213694	08/07/2001	JAPAN (with English Abstract)			$\overline{}$	×		
	AL		06/29/2001	JAPAN (with English Abstract)				×		
	AM	·	06/16/2000	JAPAN (with English Abstract)				×		
	AN		03/07/1997	JAPAN (with English Abstract)	<del></del>			X		
	AO		01/17/1997	JAPAN (with English Abstract)				X		
	AP	7-122532	05/12/1995	JAPAN (with English Abstract)				X		
	AQ	<del></del>	06/14/1994	JAPAN (with English Abstract)				×		
	AR		11/26/1993	JAPAN (with English Abstract)		Γ	$\overline{}$	×		
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		OTHER RE	EEDENCES (	Including Author, Title, Date, Pertinent	. Dames 8	• = <b>\</b>				
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	АТ		•	vol. 30, pages 1-22, "TRANSITION MET		·				
	AU	H. PRIGGE, et al., J. Electrochem. Soc., Technical Papers, Solid-State Science and Technology, vol. 138, no. 5, pages 1385-1389, "ACCEPTOR COMPENSATION IN SILICON INDUCED BY CHEMOMECHANICAL POLISHING", May 1991								
	AV	M. B. SHABANI, et al., J. Electrochem. Soc., vol. 143, no. 6, pages 2025-2029, "LOW-TEMPERATURE OUT-DIFFUSION OF Cu FROM SILICON WAFERS", June 1996								
	AW	A. A. ISTRATOV, et al., Physical Review Letters, vol. 81, no. 6, pages 1243-1246, "INTRINSIC DIFFUSION COEFFICIENT OF INTERSTITIAL COPPER IN SILICON", August 10, 1998								
	AX	C. BEAUDRY, et al., MI PROCESSES", March :	C. BEAUDRY, et al., MICRO, pages 41-54, "EVALUATING WAFER RECLAIM TECHNIQUES IN EMERGING COPPER PROCESSES", March 2000							
	AY									
Examiner	Examiner Date Considered									
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.										
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# **LIST OF RELATED CASES**

	Serial or	Filing or	Inventor/
Docket Number	Patent Number	Issue Date	<u>Applicant</u>
228953US0X	10/255,668	09/27/02	SUZUKI, et al.
243579US0X*	10/677,309	10/03/03	SUZUKI, et al.

<sup>\*</sup>Present Application; listed for information NFO/wal